## CLAIM AMENDMENTS:

Please amend Claim 1 as follows:

1. (Currently Amended) A photoelectric converting apparatus comprising:

a sensor unit including a plurality of pixels each having at least a photoelectric converter and a first amplification transistor for amplifying a signal derived from said photoelectric converter to output the amplified signal; and

a memory unit including a plurality of memories each having at least a storage element for storing therein the signal derived from said sensor unit and a second amplification transistor for amplifying a signal derived from said storage element to output an amplified signal

wherein, each of said first and second amplification transistors has a DC gain and an AC gain, wherein at least one of said DC gain and said AC gain differs between said first and second amplification transistors, and wherein said sensor unit and said memory unit output respective signals with a same gain.

 (Previously Presented) A photoelectric converting apparatus according to Claim 1, wherein said first and said second amplification transistors are constituted by MOS transistors.

- (Previously Presented) A photoelectric converting apparatus according to Claim 2, wherein said first and said second amplification transistors are connected to respective load MOS transistors.
- 4. (Previously Presented) A photoelectric converting apparatus according to Claim 3, wherein a conductance of the load MOS transistor connected to said first amplification transistor is different from a conductance of the load MOS transistor connected to said second amplification transistor.
- 5. (Previously Presented) A photoelectric converting apparatus according to Claim 4, wherein respective gate lengths of said load MOS transistors differ.
- 6. (Previously Presented) A photoelectric converting apparatus according to Claim 4, wherein respective gate widths of said load MOS transistors differ.
- (Previously Presented) A photoelectric converting apparatus
  according to Claim 4, respective gate oxide layer thicknesses of said load MOS transistors
  differ.
- 8. (Previously Presented) A photoelectric converting apparatus according to Claim 3, wherein respective conductances of said first and second amplification transistors differ.

- 9. (Previously Presented) A photoelectric converting apparatus according to Claim 8, wherein respective gate lengths of said first and second amplification transistors differ.
- 10. (Previously Presented) A photoelectric converting apparatus according to Claim 8, wherein respective gate widths of said first and second amplification transistors differ.
- 11. (Previously Presented) A photoelectric converting apparatus according to Claim 8, wherein respective gate oxide layer thicknesses of said first and second amplification transistors differ.
- 12. (Previously Presented) A photoelectric converting apparatus according to Claim 1, further comprising a transferring system for amplifying the signal derived from said sensor unit and/or said memory unit to transfer the amplified signal to said sensor unit and/or said memory unit.